74LVC2G00-Q100

Dual 2-input NAND gate

Rev. 1 — 3 September 2015 Product data sheet

1. General description

The 74LVC2G00-Q100 provides a 2-input NAND gate function.

Inputs can be driven from either 3.3 V or 5 V devices. This feature allows the use of these devices as translators in a mixed 3.3 V and 5 V environment.

This device is fully specified for partial power-down applications using I_{OFF}. The I_{OFF} circuitry disables the output, preventing the damaging backflow current through the device when it is powered down.

This product has been qualified to the Automotive Electronics Council (AEC) standard Q100 (Grade 1) and is suitable for use in automotive applications.

2. Features and benefits

- Automotive product qualification in accordance with AEC-Q100 (Grade 1)
  - Specified from −40 °C to +85 °C and from −40 °C to +125 °C
- Wide supply voltage range from 1.65 V to 5.5 V
- 5 V tolerant outputs for interfacing with 5 V logic
- High noise immunity
- ±24 mA output drive (V_{CC} = 3.0 V)
- CMOS low power consumption
- Complies with JEDEC standard:
  - JESD8-7 (1.65 V to 1.95 V)
  - JESD8-5 (2.3 V to 2.7 V)
  - JESD8-B/JESD36 (2.7 V to 3.6 V)
- Latch-up performance exceeds 250 mA
- Direct interface with TTL levels
- Inputs accept voltages up to 5 V
- ESD protection:
  - MIL-STD-883, method 3015 exceeds 2000 V
  - HBM JESD22-A114F exceeds 2000 V
  - MM JESD22-A115-A exceeds 200 V (C = 200 pF, R = 0 Ω)

3. Ordering information

Table 1. Ordering information

Type number	Package			
	Temperature range	Name	Description	Version
74LVC2G00DC-Q100	−40 °C to +125 °C	VSSOP8	plastic very thin shrink small outline package; 8 leads; body width 2.3 mm	SOT765-1

4. Marking

Table 2. Marking codes

Type number	Marking code[1]
74LVC2G00DC-Q100	V00

[1] The pin 1 indicator is located on the lower left corner of the device, below the marking code.

5. Functional diagram

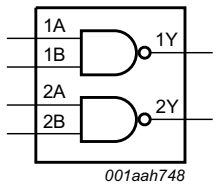


Fig 1. Logic symbol

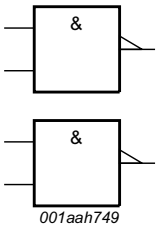


Fig 2. IEC logic symbol

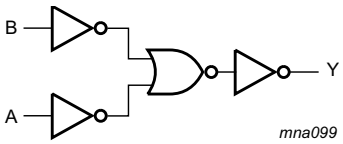


Fig 3. Logic diagram (one gate)

6. Pinning information

6.1 Pinning

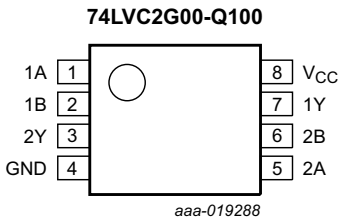


Fig 4. Pin configuration SOT765-1

6.2 Pin description

Table 3. Pin description

Symbol	Pin	Description
1A, 2A	1, 5	data input
1B, 2B	2, 6	data input
GND	4	ground (0 V)
1Y, 2Y	7, 3	data output
V_{CC}	8	supply voltage

7. Functional description

Table 4. Function table[1]

Input		Output
nA	**nB**	**nY**
L	L	H
L	H	H
H	L	H
H	H	L

[1] H = HIGH voltage level; L = LOW voltage level.

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{CC}	supply voltage			–0.5	+6.5	V
V_I	input voltage		[1]	–0.5	+6.5	V
V_O	output voltage	Active mode	[1]	–0.5	V_{CC} + 0.5	V
		Power-down mode	[1][2]	–0.5	+6.5	V
I_{IK}	input clamping current	V_I < 0 V		–50	-	mA
I_{OK}	output clamping current	V_O < 0 V or V_O > V_{CC}		-	±50	mA
I_O	output current	V_O = 0 V to V_{CC}		-	±50	mA
I_{CC}	supply current			-	100	mA
I_{GND}	ground current			–100	-	mA
T_{stg}	storage temperature			–65	+150	°C
P_{tot}	total power dissipation	T_{amb} = –40 °C to +125 °C	[3]	-	300	mW

[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] When V_{CC} = 0 V (Power-down mode), the output voltage can be 5.5 V in normal operation.

[3] For VSSOP8 package: above 110 °C the value of P_{tot} derates linearly with 8 mW/K.

9. Recommended operating conditions

Table 6. Operating conditions

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CC}	supply voltage		1.65	5.5	V
V_I	input voltage		0	5.5	V
V_O	output voltage	Active mode	0	V_{CC}	V
		Power-down mode	0	5.5	V
T_{amb}	ambient temperature		−40	+125	°C
$\Delta t/\Delta V$	input transition rise and fall rate	V_{CC} = 1.65 V to 2.7 V	-	20	ns/V
		V_{CC} = 2.7 V to 5.5 V	-	10	ns/V

10. Static characteristics

Table 7. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
T_{amb} = −40 °C to +85 °C[1]						
V_{IH}	HIGH-level input voltage	V_{CC} = 1.65 V to 1.95 V	0.65 × V_{CC}	-	-	V
		V_{CC} = 2.3 V to 2.7 V	1.7	-	-	V
		V_{CC} = 2.7 V to 3.6 V	2.0	-	-	V
		V_{CC} = 4.5 V to 5.5 V	0.7 × V_{CC}	-	-	V
V_{IL}	LOW-level input voltage	V_{CC} = 1.65 V to 1.95 V	-	-	0.35 × V_{CC}	V
		V_{CC} = 2.3 V to 2.7 V	-	-	0.7	V
		V_{CC} = 2.7 V to 3.6 V	-	-	0.8	V
		V_{CC} = 4.5 V to 5.5 V	-	-	0.3 × V_{CC}	V
V_{OH}	HIGH-level output voltage	V_I = V_{IH} or V_{IL}				
		I_O = −100 μA; V_{CC} = 1.65 V to 5.5 V	V_{CC} − 0.1	-	-	V
		I_O = −4 mA; V_{CC} = 1.65 V	1.2	1.53	-	V
		I_O = −8 mA; V_{CC} = 2.3 V	1.9	2.13	-	V
		I_O = −12 mA; V_{CC} = 2.7 V	2.2	2.50	-	V
		I_O = −24 mA; V_{CC} = 3.0 V	2.3	2.60	-	V
		I_O = −32 mA; V_{CC} = 4.5 V	3.8	4.10	-	V
V_{OL}	LOW-level output voltage	V_I = V_{IH} or V_{IL}				
		I_O = 100 μA; V_{CC} = 1.65 V to 5.5 V	-	-	0.1	V
		I_O = 4 mA; V_{CC} = 1.65 V	-	0.08	0.45	V
		I_O = 8 mA; V_{CC} = 2.3 V	-	0.14	0.3	V
		I_O = 12 mA; V_{CC} = 2.7 V	-	0.19	0.4	V
		I_O = 24 mA; V_{CC} = 3.0 V	-	0.37	0.55	V
		I_O = 32 mA; V_{CC} = 4.5 V	-	0.43	0.55	V
I_I	input leakage current	V_I = 5.5 V or GND; V_{CC} = 0 V to 5.5 V	-	±0.1	±5	μA
I_{OFF}	power-off leakage current	V_I or V_O = 5.5 V; V_{CC} = 0 V	-	±0.1	±10	μA

Table 7. Static characteristics *…continued*

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
I_{CC}	supply current	V_I = 5.5 V or GND; V_{CC} = 1.65 V to 5.5 V; I_O = 0 A	-	0.1	10	μA
ΔI_{CC}	additional supply current	per pin; $V_I = V_{CC} - 0.6$ V; I_O = 0 A; V_{CC} = 2.3 V to 5.5 V	-	5	500	μA
C_I	input capacitance		-	2.5	-	pF
T_{amb} = –40 °C to +125 °C						
V_{IH}	HIGH-level input voltage	V_{CC} = 1.65 V to 1.95 V	0.65 × V_{CC}	-	-	V
		V_{CC} = 2.3 V to 2.7 V	1.7	-	-	V
		V_{CC} = 2.7 V to 3.6 V	2.0	-	-	V
		V_{CC} = 4.5 V to 5.5 V	0.7 × V_{CC}	-	-	V
V_{IL}	LOW-level input voltage	V_{CC} = 1.65 V to 1.95 V	-	-	0.35 × V_{CC}	V
		V_{CC} = 2.3 V to 2.7 V	-	-	0.7	V
		V_{CC} = 2.7 V to 3.6 V	-	-	0.8	V
		V_{CC} = 4.5 V to 5.5 V	-	-	0.3 × V_{CC}	V
V_{OH}	HIGH-level output voltage	$V_I = V_{IH}$ or V_{IL}				
		I_O = –100 μA; V_{CC} = 1.65 V to 5.5 V	V_{CC} – 0.1	-	-	V
		I_O = –4 mA; V_{CC} = 1.65 V	0.95	-	-	V
		I_O = –8 mA; V_{CC} = 2.3 V	1.7	-	-	V
		I_O = –12 mA; V_{CC} = 2.7 V	1.9	-	-	V
		I_O = –24 mA; V_{CC} = 3.0 V	2.0	-	-	V
		I_O = –32 mA; V_{CC} = 4.5 V	3.4	-	-	V
V_{OL}	LOW-level output voltage	$V_I = V_{IH}$ or V_{IL}				
		I_O = 100 μA; V_{CC} = 1.65 V to 5.5 V	-	-	0.1	V
		I_O = 4 mA; V_{CC} = 1.65 V	-	-	0.70	V
		I_O = 8 mA; V_{CC} = 2.3 V	-	-	0.45	V
		I_O = 12 mA; V_{CC} = 2.7 V	-	-	0.60	V
		I_O = 24 mA; V_{CC} = 3.0 V	-	-	0.80	V
		I_O = 32 mA; V_{CC} = 4.5 V	-	-	0.80	V
I_I	input leakage current	V_I = 5.5 V or GND; V_{CC} = 0 V to 5.5 V	-	-	±20	μA
I_{OFF}	power-off leakage current	V_I or V_O = 5.5 V; V_{CC} = 0 V	-	-	±20	μA
I_{CC}	supply current	V_I = 5.5 V or GND; V_{CC} = 1.65 V to 5.5 V; I_O = 0 A	-	-	40	μA
ΔI_{CC}	additional supply current	per pin; $V_I = V_{CC} - 0.6$ V; I_O = 0 A; V_{CC} = 2.3 V to 5.5 V	-	-	5000	μA

[1] All typical values are measured at T_{amb} = 25 °C.

11. Dynamic characteristics

Table 8. Dynamic characteristics

Voltages are referenced to GND (ground 0 V); for test circuit see Figure 6.

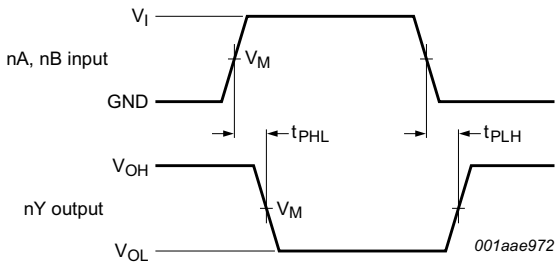
Symbol	Parameter	Conditions	–40 °C to +85 °C			–40 °C to +125 °C		Unit
			Min	Typ[1]	Max	Min	Max	
t_{pd}	propagation delay	nA, nB to nY; see Figure 5 [2]						
		V_{CC} = 1.65 V to 1.95 V	1.2	3.5	8.6	1.2	10.8	ns
		V_{CC} = 2.3 V to 2.7 V	0.7	2.3	4.8	0.7	6.0	ns
		V_{CC} = 2.7 V	0.7	3.0	5.6	0.7	7.0	ns
		V_{CC} = 3.0 V to 3.6 V	0.7	2.2	4.3	0.7	5.4	ns
		V_{CC} = 4.5 V to 5.5 V	0.5	1.8	3.3	0.5	4.2	ns
C_{PD}	power dissipation capacitance	per gate; V_I = GND to V_{CC} [3]	-	14	-	-	-	pF

[1] Typical values are measured at nominal V_{CC} and at T_{amb} = 25 °C.

[2] t_{pd} is the same as t_{PLH} and t_{PHL}

[3] C_{PD} is used to determine the dynamic power dissipation (P_D in μW).
$P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma(C_L \times V_{CC}^2 \times f_o)$ where:
f_i = input frequency in MHz;
f_o = output frequency in MHz;
C_L = output load capacitance in pF;
V_{CC} = supply voltage in V;
N = number of inputs switching;
$\Sigma(C_L \times V_{CC}^2 \times f_o)$ = sum of outputs.

12. Waveforms



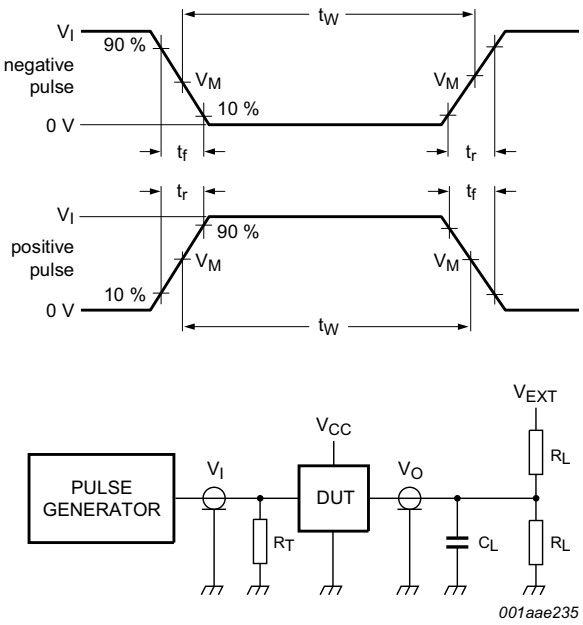
Measurement points are given in Table 9.

V_{OL} and V_{OH} are typical output voltage levels that occur with the output load.

Fig 5. Input (nA, nB) to output (nY) propagation delays

Table 9. Measurement points

Supply voltage	Input	Output
V_{CC}	V_M	V_M
1.65 V to 1.95 V	$0.5 \times V_{CC}$	$0.5 \times V_{CC}$
2.3 V to 2.7 V	$0.5 \times V_{CC}$	$0.5 \times V_{CC}$
2.7 V	1.5 V	1.5 V
3.0 V to 3.6 V	1.5 V	1.5 V
4.5 V to 5.5 V	$0.5 \times V_{CC}$	$0.5 \times V_{CC}$



Test data is given in Table 10.

Definitions for test circuit:

R_L = Load resistor.

C_L = Load capacitance including jig and probe capacitance.

R_T = Termination resistance should be equal to output impedance Z_o of the pulse generator.

V_{EXT} = Test voltage for switching times.

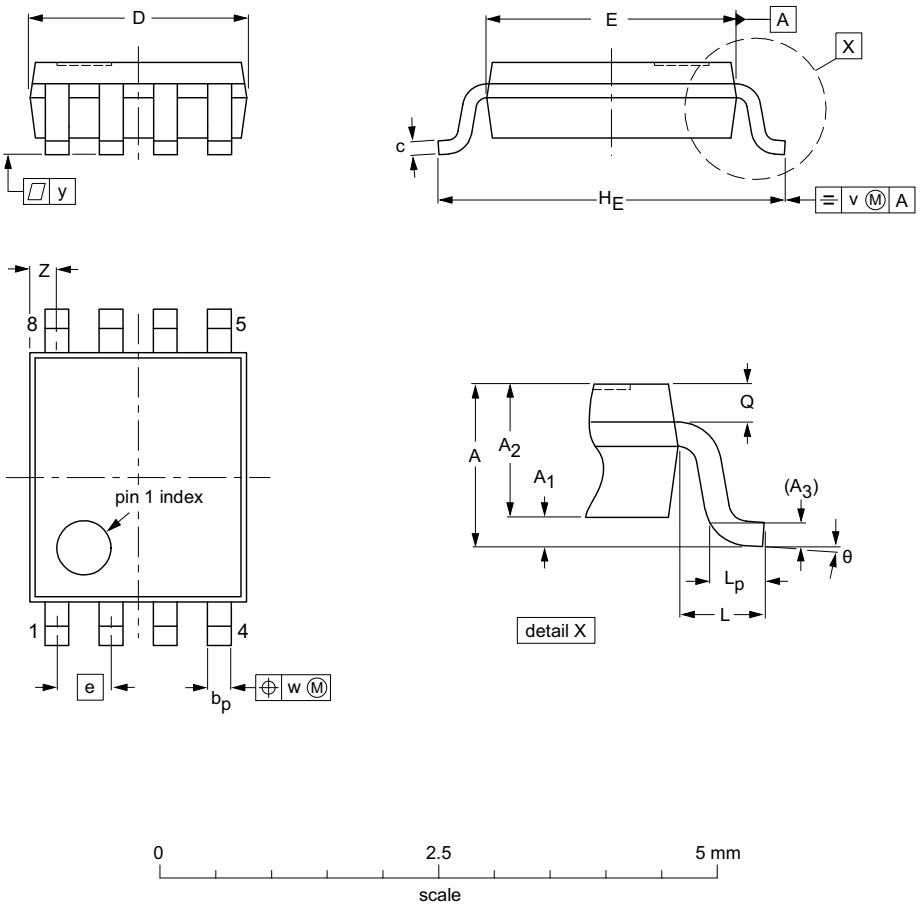
Fig 6. Test circuit for measuring switching times

Table 10. Test data

Supply voltage	Input		Load		V_{EXT}
V_{CC}	V_I	t_r, t_f	C_L	R_L	t_{PLH}, t_{PHL}
1.65 V to 1.95 V	V_{CC}	≤ 2.0 ns	30 pF	1 kΩ	open
2.3 V to 2.7 V	V_{CC}	≤ 2.0 ns	30 pF	500 Ω	open
2.7 V	2.7 V	≤ 2.5 ns	50 pF	500 Ω	open
3.0 V to 3.6 V	2.7 V	≤ 2.5 ns	50 pF	500 Ω	open
4.5 V to 5.5 V	V_{CC}	≤ 2.5 ns	50 pF	500 Ω	open

13. Package outline

VSSOP8: plastic very thin shrink small outline package; 8 leads; body width 2.3 mm **SOT765-1**



DIMENSIONS (mm are the original dimensions)

UNIT	A max.	A_1	A_2	A_3	b_p	c	$D^{(1)}$	$E^{(2)}$	e	H_E	L	L_p	Q	v	w	y	$Z^{(1)}$	θ
mm	1	0.15 0.00	0.85 0.60	0.12	0.27 0.17	0.23 0.08	2.1 1.9	2.4 2.2	0.5	3.2 3.0	0.4	0.40 0.15	0.21 0.19	0.2	0.13	0.1	0.4 0.1	8° 0°

Notes

1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.
2. Plastic or metal protrusions of 0.25 mm maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT765-1		MO-187				02-06-07

Fig 7. Package outline SOT765-1 (VSSOP8)

14. Abbreviations

Table 11. Abbreviations

Acronym	Description
CMOS	Complementary Metal Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
MIL	Military
MM	Machine Model
TTL	Transistor-Transistor Logic

15. Revision history

Table 12. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74LVC2G00_Q100 v.1	20150903	Product data sheet	-	-

16. Legal information

16.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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18. Contents

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